

54FCT/74FCT563 **Octal Latch with TRI-STATE® Outputs**

General Description

The 'FCT563 is a high-speed octal latch with buffered common Latch Enable (LE) and buffered common Output Enable (OE) inputs.

FACT FCT utilizes NSC quiet series technology to provide improved quiet output switching and dynamic threshold performance.

FACT FCT features GTO™ output control and undershoot corrector in addition to a split ground bus for superior performance.

The 'FCT563 device is functionally identical to the 'FCT573. but with inverted outputs.

Ordering Code: See Section 8

Logic Symbols

Features

- Inputs and outputs on opposite side of package allow easy interface with microprocessors
- Input clamp diodes to limit bus reflections
- TTL/CMOS input and output level compatible
- I_{OL} = 48 mA (Com), 32 mA (Mil)
- CMOS power levels
- ESD immunity \geq 4 kV typ
- Military product compliant to MIL-STD-883

D D₂ Do D3 D4 D5 D6 D7 F 01 02 03 04 05 06 02 TL/F/10670-1



IEEE/IEC



Connection Diagrams

Pin Assignment

for DIP, Flatpak and SOIC







Pin Names	Description
D ₀ -D ₇	Data Inputs
LE	Latch Enable Input
OE	TRI-STATE Output Enable Input
$\overline{O}_0 \cdot \overline{O}_7$	TRI-STATE Latch Outputs

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Functional Description

The 'FCT563 contains eight D-type latches with TRI-STATE complementary outputs. When the Latch Enable (LE) input is HIGH, data on the Dn inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable (OE) input. When OE is LOW, the buffers are in the TRI-STATE mode. When OE is HIGH the buffers are in the high impedance mode but that does not interfere with entering new data into the latches.

Function Table

	inputs		Outputs	Function		
ŌĒ	LE	D	0			
н	х	Х	Z	High-Z		
LHL		L	н	Transparent		
L	н	н	L	Transparent		
L	L	х	NC	Latched		

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance NC = No Change





Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Terminal Voltage with Respect to GND) (V _{TERM})
54FCT	-0.5V to +7.0V
74FCT	-0.5V to +7.0V
Temperature under Bias (T _{BIAS})	
74FCT	- 55°C to + 125°C
54FCT	-65°C to +135°C
Storage Temperature (T _{STG})	
74FCT	-55°C to +125°C
54FCT	-65°C to +150°C
Power Dissipation (PT)	0.5W
DC Output Current (I _{OUT})	120 mA

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. Exposure to absolute maximum rating conditions for extended periods may affect reliability. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables.

Recommended Operating Conditions

Supply Voltage (V _{CC})	
54FCT	4.5V to 5.5V
74FCT	4.75V to 5.25V
Input Voltage	0V to V _{CC}
Output Voltage	0V to V _{CC}
Operating Temperature (T _A)	
54FCT	-55°C to +125°C
74FCT	0°C to +70°C
Junction Temperature (T _{.1})	
CDIP	175°C
PDIP	140°C

DC Characteristics for 'FCT Family Devices Typical values are at $V_{CC} = 5.0V$, 25°C ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC} = 5.0V \pm 5\%$, $T_A = 0$ °C to +70°C; Mil: $V_{CC} = 5.0V \pm 10\%$ $T_A = -55$ °C to +125°C, $V_{HC} = V_{CC} - 0.2V$

Symbol	Parameter	54FCT/74FCT			Units	Conditions		
Symbol		Min Typ Max		Conditions				
VIH	Minimum High Level Input Voltage	2.0			v			
VIL	Maximum Low Level Input Voltage			0.8	v			
ін	Input High Current			5.0 5.0	μΑ	V _{CC} = Max	V _I = V _{CC} V _I = 2.7V (Note 2)	
l _{iL}	Input Low Current			5.0 5.0	μA	V _{CC} = Max	$V_I = 0.5V$ (Note 2) $V_I = GND$	
loz	Maximum TRI-STATE Current			10.0 10.0 - 10.0 - 10.0	μΑ	V _{CC} = Max	$V_{O} = V_{CC}$ $V_{O} = 2.7V \text{ (Note 2)}$ $V_{O} = 0.5V \text{ (Note 2)}$ $V_{O} = \text{GND}$	
V _{IK}	Clamp Diode Voltage		-0.7	-1.2	V	$V_{CC} = Min; I_N = -18 \text{ mA}$		
los	Short Circuit Current	-60	- 120		mA	V _{CC} = Max (Note 1); V _O = GND		
V _{OH}	Minimum High Level	2.8	3.0			$V_{CC} = 3V$; $V_{IN} = 0.2V$ or V_{HC} ; $I_{OH} = -32 \mu A$		
	2.	V _{HC}	V _{CC}			V _{CC} = Min	l _{OH} = −300 μA	
		2.4	4.3		v	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -12 \text{ mA}$ (Mil)	
		2.4	4.3				$I_{OH} = -15 \text{ mA} \text{ (Com)}$	
V _{OL}	Maximum Low Level		GND	0.2		$V_{CC} = 3V; V_{IN} = 0.2$	V or V _{HC} ; $I_{OL} = 300 \ \mu A$	
	Output Voltage		GND	GND 0.2	v	V _{CC} = Min	I _{OL} = 300 μA	
			0.3	0.50		$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 32 mA (Mil)	
			0.3	0.50			$I_{OL} = 48 \text{ mA} \text{ (Com)}$	

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DC Characteristics for FCT Family Devices (Continued) Typical values are at $V_{CC} = 5.0V$, 25°C ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC} = 5.0V \pm 5\%$, $T_A = 0$ °C to +70°C; Mil: $V_{CC} = 5.0V \pm 10\%$ $T_A = -55$ °C to + 125°C, $V_{HC} = V_{CC} - 0.2V$

	ol Parameter	74FCT			Units	Conditions	
Symbol		Min	Тур	Max	Units	Conditions	
lcc	Maximum Quiescent Supply Current	1	0.001	1.5	mA	$\label{eq:VCC} \begin{array}{l} V_{CC} = Max \\ V_{IN} \geq V_{HC} \leq 0.2V \\ \mathfrak{f}_I = 0 \end{array}$	
∆l _{CC}	Quiescent Supply Current; TTL Inputs HIGH		0.5	2.0	mA	V _{CC} = Max V _{IN} = 3.4V (Note 3)	
ICCD	Dynamic Power Supply Current (Note 4)		0.25	0.45	mA/MHz	$V_{CC} = Max$ Outputs Open $\overline{OE} = GND$ $LE = V_{CC}$ One Input Toggling 50% Duty Cycle	$V_{IN} \ge V_{HC}$ $V_{IN} \le 0.2V$
lc	Total Power Supply Current (Note 6)		1.5	4.5	mA	$V_{CC} = Max$ Outputs Open $\overline{OE} = GND$	$V_{IN} \ge V_{HC}$ $V_{IN} \le 0.2V$
			1.8	5.0		$LE = V_{CC}$ $\dot{f}_I = 10 \text{ MHz}$ One Bit Toggling 50% Duty Cycle	$V_{IN} = 3.4V$ $V_{IN} = GND$
			3.0	8.0		(Note 5) $V_{CC} = Max$ Outputs Open $\overline{OE} = GND$	$V_{IN} \ge V_{HC}$ $V_{IN} \le 0.2V$
			5.0	14.5		$\begin{array}{l} LE = V_{CC} \\ f_{I} = 2.5 \ MHz \\ Eight \ Bits \ Toggling \\ 50\% \ Duty \ Cycle \end{array}$	$V_{IN} = 3.4V$ $V_{IN} = GND$
v _H	Input Hysteresis on LE Only	-	200		mV		

I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

f_I = Input Frequency NI = Number of Inputs at fi

All currents are in milliamps and all frequencies are in megahertz.

Note 7: For 54FCT, I_{CCD} = 0.40 mA/MHz.

Refer to applicable standard military drawing or NSC Table I for test conditions and I_C/I_{CC} limits.

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		54FCT/74FCT	74	FCT	54FCT $T_A, V_{CC} = Mil$ $R_L = 500\Omega$ $C_L = 50 pF$		Units	
Symbol	Parameter	$T_{A} = 25^{\circ}C$ $V_{CC} = 5.0V$	R _L =	c = Com 500Ω 50 pF				Fig. No.
		Тур	Min (No	te 1) Max	Min	Max	1	
t _{PLH} t _{PHL}	Propagation Delay D_n to \overline{O}_n	5.0	1.5	8.0			ns	2-8
t _{PLH} t _{PHL}	Propagation Delay LE to \overline{O}_n	9.0	2.0	13.0			ns	2-8
t _{PZL} t _{PZH}	Output Enable Time	7.0	1.5	12.0			ns	2-11
t _{PHZ} t _{PLZ}	Output Disable Time	6.0	1.5	7.5			ns	2-11
ts	Set Up Tme High or Low D _n to LE	1.0	2.0	-			ns	2-11
t _Η	Hold Time High or Low D _n to LE	1.0	1.5	_			ns	2-10
tw	LE Pulse Width High or Low	5.0	6.0	_			ns	2-9

Note 1: Minimum limits are guaranteed but not tested on propagation delays.

Capacitance $T_A = +25^{\circ}C$, f = 1.0 MHz

Symbol	Symbol Parameter		Max	Units	Conditions
C _{IN}	Input Capacitance	6	10	ρF	$V_{IN} = 0V$
COUT	Output Capacitance	8	12	pF	$V_{OUT} = 0V$

Note: This parameter is measured at characterization but not tested. $C_{\mbox{OUT}}$ for 74FCT only.

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